

Initial Information Data Sheet

Inventor Information

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Application Information

Title Line One:: Gallium Nitride Semiconductor Light
Title Line Two:: Emitting Device Having Multi-Quantum
Title Line Three:: -Well Structure Active Layer, And
Title Line Four:: Semiconductor Laser Light Source Device
Total Drawing Sheets:: 10
Formal Drawings?:: Yes
Application Type:: Utility
Docket Number:: 204552016410

Representative Information

Representative Customer Number:: 25227

Continuity Information

This application is a:: Continuation of
> Application One:: 09/380,537
Filing Date:: September 2, 1999

which is a:: 371 of
>>Application Two:: PCT/JP98/00828
Filing Date:: February 27, 1998

Prior Foreign Applications

Foreign Application One:: JP 9-52596
Filing Date:: March 7, 1997
Country:: Japan
Priority Claimed:: Yes

Foreign Application Two:: JP 9-65725
Filing Date:: March 19, 1997
Country:: Japan
Priority Claimed:: Yes